AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (original): An electrode for use in a gallium nitride-based compound semiconductor light-emitting device comprising a light-permeable first layer which is in contact with a surface of a p-contact layer in a gallium nitride-based compound semiconductor light-emitting device and which is capable of providing ohmic contact, and a second layer which is in contact with a part of a surface of said p-contact layer, wherein said first layer comprises a metal, or an alloy of two or more metals, selected from a first group consisting of Au, Pt, Pd, Ni, Co, and Rh, and said second layer comprises an oxide of at least one metal selected from a second group consisting of Ni, Ti, Sn, Cr, Co, Zn, Cu, Mg, and In.

2. (original): An electrode according to claim 1, wherein said first layer further comprises Ga.

3. (original): An electrode according to claim 1, wherein a portion of the surface of said p-contact layer, which portion is not in contact with said second layer, includes an oxygen-lacking portion.

4. (original): An electrode according to claim 1, which further comprises a third layer on a surface of said first layer opposite the side in contact with said p-contact layer, said third layer comprising an oxide of at least one metal selected from said second group.

5. (original): An electrode according to claim 1, wherein said first layer comprises an alloy of Au with Ni and/or Co.

6. (original): An electrode according to claim 1, wherein said second layer comprises an oxide of Ni and/or Co.

7. (original): An electrode according to claim 4, wherein said third layer comprises an oxide of Ni and/or Co.

8. (original): An electrode according to claim 1, wherein said second layer accounts for 0.01 to 90% of the surface of said p-contact layer.

9. (original): An electrode according to claim 3, wherein said oxygen-lacking portion accounts for 10% or more of the surface of said p-contact layer.

10. (original): An electrode according to claim 1, wherein said second layer has a thickness of 0.1 to 100 nm.

11. (original): An electrode according to claim 5, wherein said alloy of said first layer has an Ni and/or Co content of 0.01 to 70 atom %.

12. (original): An electrode according to claim 1, wherein said first layer has a thickness of 0.1 to 100 nm.

13. (original): An electrode according to claim 4, wherein said third layer has a thickness of 1 nm or more.

14. (original): An electrode according to claim 1, wherein said first layer has one or more pores in a portion thereof.

15. (original): An electrode according to claim 1, wherein said first layer has a thick portion and a thin portion.

16. (currently amended): A gallium nitride-based compound semiconductor light-emitting device comprising an n-contact layer, a light-emitting layer and a p-contact layer formed on a substrate, which are composed of a gallium nitride-based compound semiconductor and which are sequentially stacked in the above order, and a negative electrode and a positive electrode which are formed on a surface of said n-contact layer and a surface of said p-contact layer, respectively, wherein said positive electrode is formed of an electrode according to claim 1~~any one of claims 1 to 15~~.